



501.26244CC7

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: MURATA, et al.  
Serial No.: 09/998,654  
Filed: December 3, 2001  
For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE HAVING  
SWITCHING MISFET AND CAPACITOR ELEMENT AND  
METHOD OF PRODUCING THE SAME, INCLUDING WIRING  
THEREFOR AND METHOD OF PRODUCING SUCH WIRING  
Group: 2812  
Examiner: H. Tsai

AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, A 22313-1450

RECEIVED  
JUL 25 2003  
SEMICONDUCTOR CENTER 2800  
July 24, 2003

Sir:

In response to the Office Action mailed January 24, 2003, please amend the  
above-identified application as follows:

IN THE CLAIMS

Please amend the claims presently in the application as follows:

1. (Amended) A method of producing a semiconductor integrated circuit  
device having word lines, data lines and a plurality of memory cells each connected to  
one of the word lines and one of the data lines, each of said plurality of memory cells  
having (1) a MISFET having a gate electrode and a source region and a drain region on